

RF AMPLIFIER

MODEL *TM6670PM*

Available as: TM6670PM, 4 Pin TO-8 (T4)
 TN6670PM, 4 Pin Surface Mount (SM3)
 FP6670PM, 4 Pin Flatpack (FP4)
 BX6670PM, Connectorized Housing (H1)

Features

- Superior Phase Noise Performance
- Low Noise Figure: 1.8 dB Typical
- Operating Temp. -55 °C to +85 °C
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C
Frequency	10 - 300 MHz	10 - 300 MHz
Gain (dB)	8	6 Min.
Power @ 1 dB Comp. (dBm)	20	18 Min.
Reverse Isolation (dB)	-11	-10 Max.
VSWR In	<1.5:1	2.5:1 Max.
VSWR Out	<1.5:1	2.5:1 Max.
Noise Figure (dB)	1.8	3 Max.
Power Vdc	+15	+15
mA	25	30 Max.

Note: Care should always be taken to effectively ground the case of each unit.

Typical Intermodulation Performance at 25 °C

Second Order Harmonic Intercept Point +52 dBm (Typ.)
 Second Order Two Tone Intercept Point +46 dBm (Typ.)
 Third Order Two Tone Intercept Point +36 dBm (Typ.)

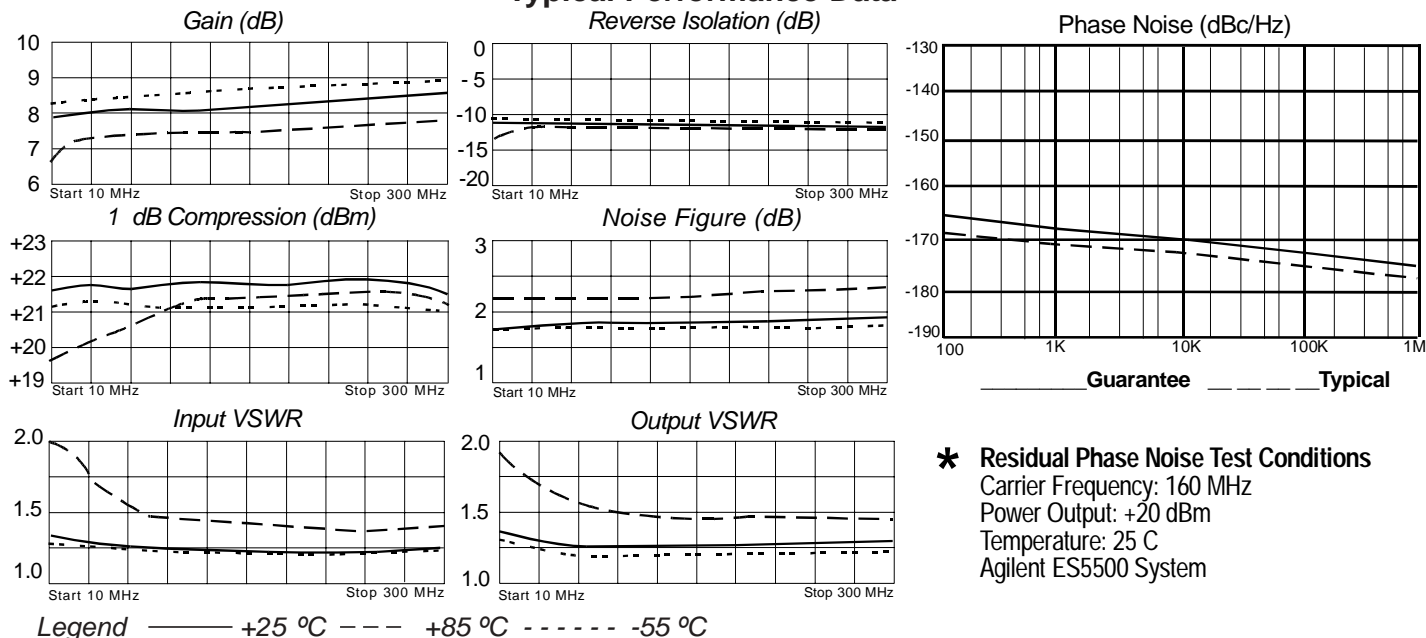
Maximum Ratings

Ambient Operating Temperature -55°C to +100 °C
 Storage Temperature -62°C to +125 °C
 Case Temperature +125 °C
 DC Voltage +18 Volts
 Continuous RF Input Power +13 dBm
 Short Term RF Input Power 50 Milliwatts (1 Minute Max.)
 Maximum Peak Power 0.5 Watt (3 µsec Max.)

Guaranteed Phase Noise Performance (dBc/Hz)

Frequency	Typical	Guarantee
100 Hz	-169	-166
1 kHz	-171	-168
10 kHz	-172	-169
100 kHz	-176	-173
1 MHz	-177	-174

Typical Performance Data



* Residual Phase Noise Test Conditions
 Carrier Frequency: 160 MHz
 Power Output: +20 dBm
 Temperature: 25 C
 Agilent ES5500 System

Linear S-Parameters

FREQ. MHz	S11		S21		S12		S22	
	Mag	Deg	Mag	Deg	Mag	Deg	Mag	Deg
5	.19	138	2.48	17	.28	18	.21	141
10	.12	146	2.56	8	.29	8	.13	144
20	.09	160	2.58	1	.29	2	.10	159
50	.08	-179	2.60	-7	.29	-7	.08	173
100	.11	-164	2.60	-18	.29	-17	.08	-171
150	.14	-164	2.62	-27	.28	-27	.09	-160
200	.19	-167	2.64	-37	.27	-37	.11	-149
250	.25	-175	2.67	-48	.26	-47	.16	-149
300	.32	177	2.67	-59	.25	-58	.21	-152

